

### **Change in the parameters of electron-irradiated 4H-SiC schottky diodes as a function of the time during low-temperature isothermal annealing**

**Korolkov, Oleg**; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Toompuu, Jana**; **Sleptsuk, Natalja**; **Rang, Toomas** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018, Birmingham, UK 2019 / p. 734-737 <https://doi.org/10.4028/www.scientific.net/MSF.963.734> [Conference proceeding at Scopus](#)  
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### **Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0.9 MeV electrons**

Lebedev, Alexander A.; Davidovskaja, Klavdia; Kozlovski, Vitali V.; **Korolkov, Oleg**; **Sleptšuk, Natalja**; **Toompuu, Jana** Silicon Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 447-450 : ill  
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### **Dependence of the carrier removal rate in 4H-SiC PN structures on irradiation temperature**

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### **Influence of the proton irradiation temperature on the characteristics of high-power high-voltage silicon carbide schottky diodes**

Kozlovski, Vitali V.; **Korolkov, Oleg**; Davydovskaya, Klavdia S.; Lebedev, Alexander A.; Levinshtein, Michael E.; **Sleptšuk, Natalja**; Strel'Chuk, Anatolii M.; **Toompuu, Jana** Technical Physics Letter 2020 / p. 287 - 289 <https://doi.org/10.1134/S1063785020030244>  
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